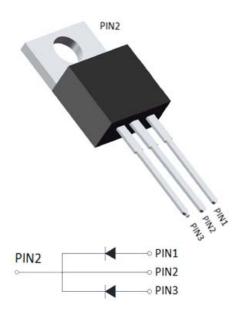






Schottky Diodes



Features

- High frequency operation
- High purity, high temperature epoxy encapsulation for enhanced mechanical strength and moisture resistance
- Guard ring for enhanced ruggedness and long term reliability
- Solder dip 275 °C max. 7 s, per JESD 22-B106

Typical Applications

Typical applications are in switching power supplies, converters, freewheeling diodes, and reverse battery protection.

Mechanical Data

• Package: TO-220AB

Molding compound meets UL 94 V-0 flammability

rating, RoHS-compliant

• Terminals: Tin plated leads, solderable per J-STD-

002 and JESD22-B102
• Polarity: As marked

■Maximum Ratings (Ta=25°C Unless otherwise specified)

= maximum ratings (1a 25 6 5 most state mest specimes)						
PARAMETER	SYMBOL	UNIT	MBR2060CT			
Device marking code			MBR2060CT			
Repetitive Peak Reverse Voltage	VRRM	V	60			
Average Rectified Output Current @60Hz sine wave, R-load, Ta=25°C	IO	Α	20			
Surge(Non-repetitive)Forward Current @60H _Z half sine-wave,1 cycle, T _a =25 [°] C	IFSM	Α	150			
Current Squared Time @1ms≤t<8.3ms Tj=25℃,	I ² t	A ² s	94			
Storage Temperature	T _{stg}	$^{\circ}$	-55 ~ + 150			
Junction Temperature Tj		°C	-55 ~ + 150			

■Electrical Characteristics (Ta=25°C Unless otherwise specified)

==:ouriour orial actoriones () a = ouriour ouriour operation				
PARAMETER	SYMBOL	UNIT	TEST CONDITIONS	MBR2060CT
Maximum instantaneous forward voltage drop per diode	VFM	V	IFM=10.0A	0.72
Maximum DC reverse current at rated DC blocking voltage per	IRRM1	mA ·	VRM=VRRM T _a =25℃	0.2
diode	IRRM2		VRM=VRRM T _a =125°C	50

MBR2060CT

Thermal Characteristics $(T_a=25^{\circ}\mathbb{C} \text{ Unless otherwise specified})$

PARAMETER		SYMBOL	UNIT	MBR2060CT
Thermal Resistance	Between junction and case	RθJ-c	°C/W	2.0

■Ordering Information (Example)

PREFERED P/N	UNIT WEIGHT(g)	MINIIMUM PACKAGE(pcs)	INNER BOX QUANTITY(pcs)	OUTER CARTON QUANTITY(pcs)	DELIVERY MODE
MBR2060CT	Approximate 1.9	50	1000	5000	Tube

■Characteristics (Typical)

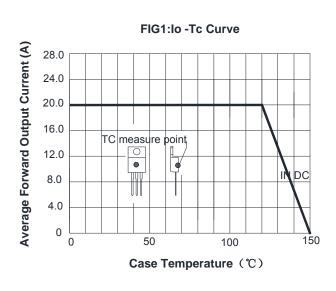
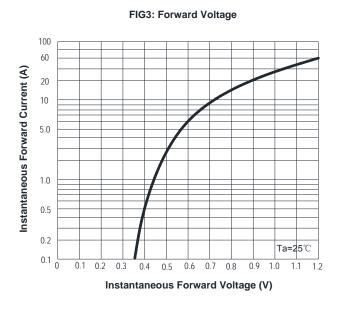
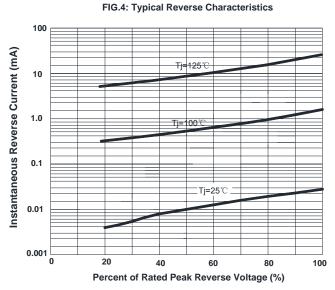


FIG2:Surge Forward Current Capability 175 Peak Forward Surge Current (A) 150 125 8.3ms Single Half Sine-Wave 100 JEDEC Method 75 50 25 2 10 20 50 100 **Number of Cycles**

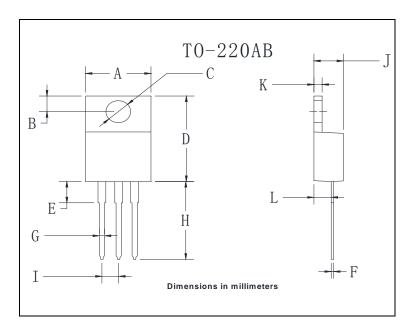




2/3



■Outline Dimensions



TO-220AB					
Dim	Min	Max			
Α	9.5	10.9			
В	2.22	3.27			
С	3.34	4.31			
D	14.5	15.5			
Е	3.16	4.46			
F	0.28	0.64			
G	0.68	0.94			
Н	13.06	14.62			
I	2.01	3.07			
J	4.04	5.1			
K	1.14	1.4			
L	2.14	3.19			

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